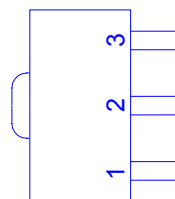
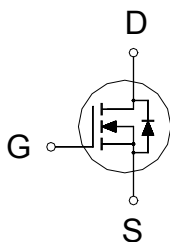


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
25	50m Ω	6A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	6	A
	$T_C = 100\text{ }^\circ\text{C}$		4	
Pulsed Drain Current ¹		I_{DM}	20	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	3	W
	$T_C = 100\text{ }^\circ\text{C}$		1.2	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Lead Temperature (¹ / ₁₆ " from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		18	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		160	

¹Pulse width limited by maximum junction temperature.²Duty cycle $\leq 1\%$ ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	25			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.8	1.2	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			25	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			250	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	6			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 3A$		70	115	m Ω
		$V_{GS} = 10V, I_D = 6A$		48	85	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 15V, I_D = 6A$		16		S

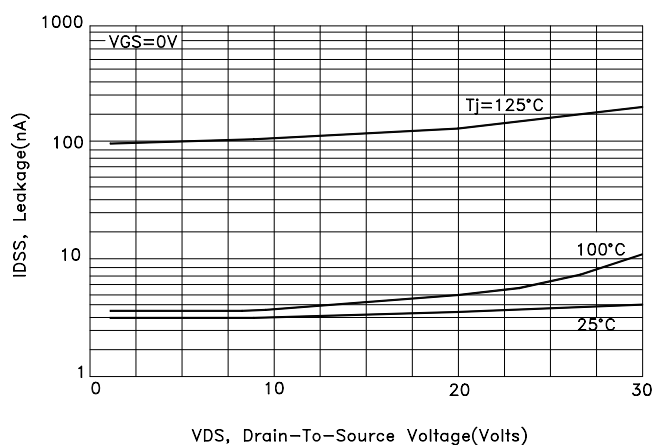
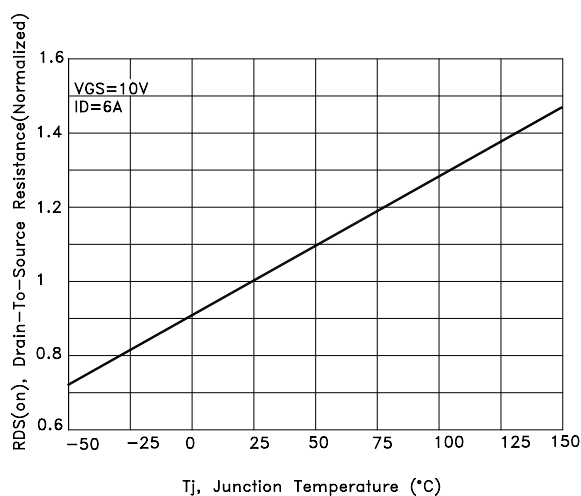
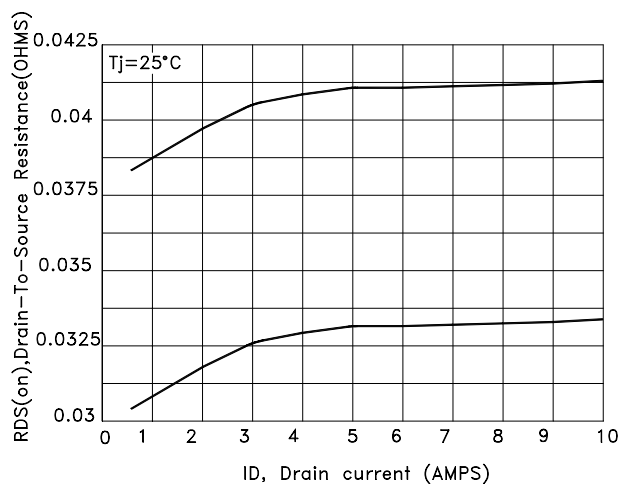
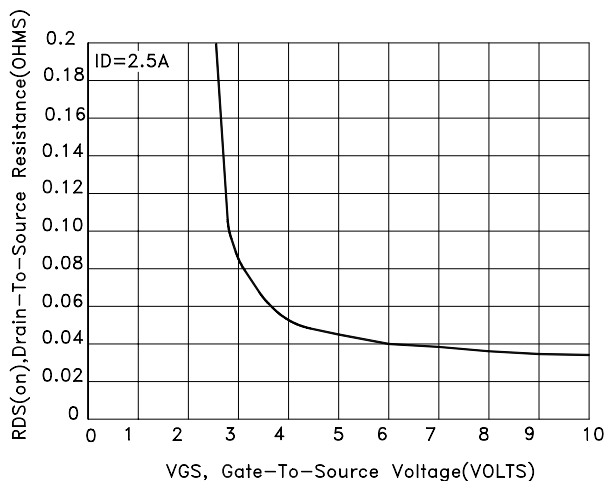
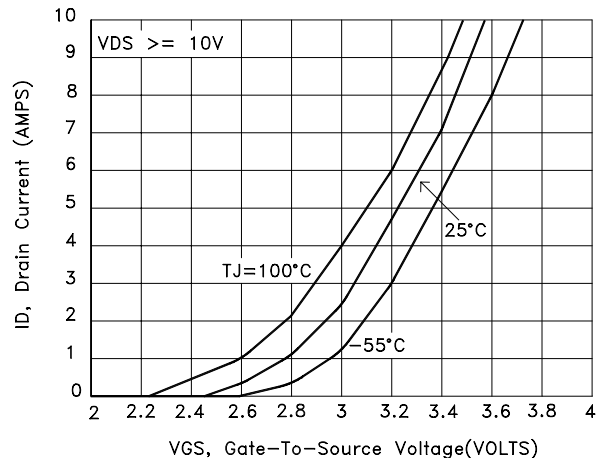
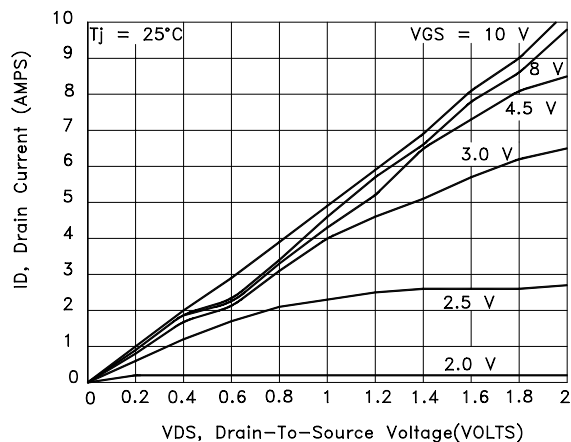
DYNAMIC

Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		450		pF
Output Capacitance	C_{oss}			200		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge ²	Q_g	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$ $I_D = 6A$		15		nC
Gate-Source Charge ²	Q_{gs}			2.0		
Gate-Drain Charge ²	Q_{gd}			7.0		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, R_L = 1\Omega$ $I_D \cong 12A, V_{GS} = 10V, R_{GS} = 2.5\Omega$		6.0		nS
Rise Time ²	t_r			6.0		
Turn-Off Delay Time ²	$t_{d(off)}$			20		
Fall Time ²	t_f			5.0		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25^\circ C$)

Continuous Current	I_S				2.3	A
Pulsed Current ³	I_{SM}				4	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.5	V

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Pulse width limited by maximum junction temperature.**REMARK: THE PRODUCT MARKED WITH "P3057G", DATE CODE or LOT #****Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.**



SOT-89 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.3	4.5	4.7	H	1.4	1.5	1.6
B	1.6	1.7	1.8	I	2.8	3.0	3.2
C	0.4	0.5	0.6	J	1.3	1.5	1.7
D	2.4	2.5	2.6	K	3.8	4.2	4.6
E	0.8	1.2	1.4	L	0.3	0.4	0.5
F	0.4	0.45	0.5	M			
G	0.4	0.5	0.6	N			

